IN THE CLAIMS:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming a passivation film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the passivation film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

2. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming a passivation film covering a surface of the wiring;

forming a leveling film containing a siloxane structure on the passivation film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

3. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming a passivation film deposited on the wiring;

forming a leveling film containing a siloxane structure on the passivation film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

4. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the insulating film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

5. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer

insulating film on the interlayer insulating film;

forming an insulating film covering a surface of the wiring;

forming a leveling film containing a siloxane structure on the insulating film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

6. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film deposited on the wiring;

forming a leveling film containing a siloxane structure on the insulating film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

7. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the insulating film; ~~and~~

forming a pixel electrode connecting the wiring through a second hole in the insulating film

and the leveling film over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

8. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the insulating film;

forming a pixel electrode connecting the wiring through a second hole in the insulating film and the leveling film over the leveling film; ~~and~~

forming an electro luminescence layer over the pixel electrode; and

forming a cathode made of a conductive film having a light-shielding property.

9. (Previously Presented) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a first hole in the interlayer insulating film on the interlayer insulating film;

forming a first insulating film directly formed on the wiring;

forming a leveling film containing a siloxane structure on the first insulating film;

forming a pixel electrode connecting the wiring through a second hole in the first insulating film and the leveling film over the leveling film; ~~and~~

forming a second insulating film over the pixel electrode; and

forming an electro luminescence layer over the pixel electrode and the second insulating film.

10. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming a passivation film directly formed on the wiring;

forming a leveling film formed by a spin coating method on the passivation film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

11. (canceled)

12. (previously presented) The method according to claim 1, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

13. (canceled)

14. (previously presented) The method according to claim 2, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

15. (canceled)

16. (previously presented) The method according to claim 3, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

17. (canceled)

18. (previously presented) The method according to claim 4, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

19. (canceled)

20. (previously presented) The method according to claim 5, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

21. (canceled)

22. (previously presented) The method according to claim 6, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

23. (canceled)

24. (previously presented) The method according to claim 7, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

25. (canceled)

26. (previously presented) The method according to claim 8, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

27. (canceled)

28. (previously presented) The method according to claim 9, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

29. (canceled)

30. (previously presented) The method according to claim 10, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

31. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming a passivation film covering a surface of the wiring;

forming a leveling film formed by a spin coating method on the passivation film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

32. (previously presented) The method according to claim 31, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

33. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming a passivation film deposited on the wiring;

forming a leveling film formed by a spin coating method on the passivation film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

34. (Previously Presented) The method according to claim 33, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

35. (Previously Presented) The method according to claim 1, wherein the wiring is formed by a sputtering method.

36. (Previously Presented) The method according to claim 1, wherein the wiring comprises aluminum.

37. (Currently Amended) The method according to claim 1, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

38. (Previously Presented) The method according to claim 1, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

39. (Previously Presented) The method according to claim 1, wherein the passivation film has a thickness of 50 to 500nm.

40. (Previously Presented) The method according to claim 1, wherein the passivation film has a thickness of 200 to 300nm.

41. (Previously Presented) The method according to claim 1, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

42. (Previously Presented) The method according to claim 1, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

43. (Previously Presented) The method according to claim 1, wherein the pixel electrode is made of a conductive oxide film.

44. (Previously Presented) The method according to claim 2, wherein the wiring is formed by a sputtering method.

45. (Previously Presented) The method according to claim 2, wherein the wiring comprises aluminum.

46. (Currently Amended) The method according to claim 2, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium, an aluminum film and a second ~~tantalum~~ titanium.

47. (Previously Presented) The method according to claim 2, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

48. (Previously Presented) The method according to claim 2, wherein the passivation film has

a thickness of 50 to 500nm.

49. (Previously Presented) The method according to claim 2, wherein the passivation film has a thickness of 200 to 300nm.

50. (Previously Presented) The method according to claim 2, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

51. (Previously Presented) The method according to claim 2, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

52. (Previously Presented) The method according to claim 2, wherein the pixel electrode is made of a conductive oxide film.

53. (Previously Presented) The method according to claim 3, wherein the wiring is formed by a sputtering method.

54. (Previously Presented) The method according to claim 3, wherein the wiring comprises aluminum.

55. (Currently Amended) The method according to claim 3, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

56. (Previously Presented) The method according to claim 3, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

57. (Previously Presented) The method according to claim 3, wherein the passivation film has a thickness of 50 to 500nm.

58. (Previously Presented) The method according to claim 3, wherein the passivation film has a thickness of 200 to 300nm.

59. (Previously Presented) The method according to claim 3, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

60. (Previously Presented) The method according to claim 3, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

61. (Previously Presented) The method according to claim 3, wherein the pixel electrode is made of a conductive oxide film.

62. (Previously Presented) The method according to claim 4, wherein the wiring is formed by a sputtering method.

63. (Previously Presented) The method according to claim 4, wherein the wiring comprises

aluminum.

64. (Currently Amended) The method according to claim 4, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

65. (Previously Presented) The method according to claim 4, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

66. (Previously Presented) The method according to claim 4, wherein the insulating film has a thickness of 50 to 500nm.

67. (Previously Presented) The method according to claim 4, wherein the insulating film has a thickness of 200 to 300nm.

68. (Previously Presented) The method according to claim 4, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

69. (Previously Presented) The method according to claim 4, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

70. (Previously Presented) The method according to claim 4, wherein the pixel electrode is made of a conductive oxide film.

71. (Previously Presented) The method according to claim 5, wherein the wiring is formed by a sputtering method.

72. (Previously Presented) The method according to claim 5, wherein the wiring comprises aluminum.

73. (Currently Amended) The method according to claim 5, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

74. (Previously Presented) The method according to claim 5, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

75. (Previously Presented) The method according to claim 5, wherein the insulating film has a thickness of 50 to 500nm.

76. (Previously Presented) The method according to claim 5, wherein the insulating film has a thickness of 200 to 300nm.

77. (Previously Presented) The method according to claim 5, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

78. (Previously Presented) The method according to claim 5, wherein the method further

comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

79. (Previously Presented) The method according to claim 5, wherein the pixel electrode is made of a conductive oxide film.

80. (Previously Presented) The method according to claim 6, wherein the wiring is formed by a sputtering method.

81. (Previously Presented) The method according to claim 6, wherein the wiring comprises aluminum.

82. (Currently Amended) The method according to claim 6, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

83. (Previously Presented) The method according to claim 6, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

84. (Previously Presented) The method according to claim 6, wherein the insulating film has a thickness of 50 to 500nm.

85. (Previously Presented) The method according to claim 6, wherein the insulating film has a thickness of 200 to 300nm.

86. (Previously Presented) The method according to claim 6, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

87. (Previously Presented) The method according to claim 6, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

88. (Previously Presented) The method according to claim 6, wherein the pixel electrode is made of a conductive oxide film.

89. (Previously Presented) The method according to claim 7, wherein the wiring is formed by a sputtering method.

90. (Previously Presented) The method according to claim 7, wherein the wiring comprises aluminum.

91. (Currently Amended) The method according to claim 7, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

92. (Previously Presented) The method according to claim 7, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

93. (Previously Presented) The method according to claim 7, wherein the insulating film has a thickness of 50 to 500nm.

94. (Previously Presented) The method according to claim 7, wherein the insulating film has a thickness of 200 to 300nm.

95. (Previously Presented) The method according to claim 7, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

96. (Previously Presented) The method according to claim 7, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

97. (Previously Presented) The method according to claim 7, wherein the second hole is formed by a dry etching method.

98. (Previously Presented) The method according to claim 7, wherein the pixel electrode is made of a conductive oxide film.

99. (Previously Presented) The method according to claim 8, wherein the wiring is formed by a sputtering method.

100. (Previously Presented) The method according to claim 8, wherein the wiring comprises aluminum.

101. (Currently Amended) The method according to claim 8, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

102. (Previously Presented) The method according to claim 8, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

103. (Previously Presented) The method according to claim 8, wherein the insulating film has a thickness of 50 to 500nm.

104. (Previously Presented) The method according to claim 8, wherein the insulating film has a thickness of 200 to 300nm.

105. (Previously Presented) The method according to claim 8, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

106. (Previously Presented) The method according to claim 8, wherein the method further comprises a step of forming another leveling film containing a siloxane structure on the leveling film.

107. (Previously Presented) The method according to claim 8, wherein the second hole is formed by a dry etching method.

108. (Previously Presented) The method according to claim 8, wherein the pixel electrode is made of a conductive oxide film.

109. (Previously Presented) The method according to claim 9, wherein the wiring is formed by a sputtering method.

110. (Previously Presented) The method according to claim 9, wherein the wiring comprises aluminum.

111. (Currently Amended) The method according to claim 9, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

112. (Previously Presented) The method according to claim 9, wherein the first insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

113. (Previously Presented) The method according to claim 9, wherein the first insulating film has a thickness of 50 to 500nm.

114. (Previously Presented) The method according to claim 9, wherein the first insulating film has a thickness of 200 to 300nm.

115. (Previously Presented) The method according to claim 9, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

116. (Previously Presented) The method according to claim 9, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

117. (Previously Presented) The method according to claim 9, wherein the second hole is formed by a dry etching method.

118. (Previously Presented) The method according to claim 9, wherein the pixel electrode is made of a conductive oxide film.

119. (Previously Presented) The method according to claim 10, wherein the wiring is formed by a sputtering method.

120. (Previously Presented) The method according to claim 10, wherein the wiring comprises aluminum.

121. (Currently Amended) The method according to claim 10, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

122. (Previously Presented) The method according to claim 10, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

123. (Previously Presented) The method according to claim 10, wherein the passivation film has a thickness of 50 to 500nm.

124. (Previously Presented) The method according to claim 10, wherein the passivation film has a thickness of 200 to 300nm.

125. (Previously Presented) The method according to claim 10, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

126. (Previously Presented) The method according to claim 10, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

127. (Previously Presented) The method according to claim 10, wherein the leveling film comprises an inorganic spin on glass material.

128. (Previously Presented) The method according to claim 10, wherein the pixel electrode is made of a conductive oxide film.

129. (Previously Presented) The method according to claim 31, wherein the wiring is formed by a sputtering method.

130. (Previously Presented) The method according to claim 31, wherein the wiring comprises aluminum.

131. (Currently Amended) The method according to claim 31, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

132. (Previously Presented) The method according to claim 31, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

133. (Previously Presented) The method according to claim 31, wherein the passivation film has a thickness of 50 to 500nm.

134. (Previously Presented) The method according to claim 31, wherein the passivation film has a thickness of 200 to 300nm.

135. (Previously Presented) The method according to claim 31, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

136. (Previously Presented) The method according to claim 31, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

137. (Previously Presented) The method according to claim 31, wherein the leveling film comprises an inorganic spin on glass material.

138. (Previously Presented) The method according to claim 31, wherein the pixel electrode is made of a conductive oxide film.

139. (Previously Presented) The method according to claim 33, wherein the wiring is formed by a sputtering method.

140. (Previously Presented) The method according to claim 33, wherein the wiring comprises aluminum.

141. (Currently Amended) The method according to claim 33, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

142. (Previously Presented) The method according to claim 33, wherein the passivation film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

143. (Previously Presented) The method according to claim 33, wherein the passivation film has a thickness of 50 to 500nm.

144. (Previously Presented) The method according to claim 33, wherein the passivation film has a thickness of 200 to 300nm.

145. (Previously Presented) The method according to claim 33, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

146. (Previously Presented) The method according to claim 33, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

147. (Previously Presented) The method according to claim 33, wherein the leveling film comprises an inorganic spin on glass material.

148. (Previously Presented) The method according to claim 33, wherein the pixel electrode is made of a conductive oxide film.

149. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film directly formed on the wiring;

forming a leveling film formed by a spin coating method on the insulating film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

150. (Previously Presented) The method according to claim 149, wherein the wiring is formed by a sputtering method.

151. (Previously Presented) The method according to claim 149, wherein the wiring comprises aluminum.

152. (Currently Amended) The method according to claim 149, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

153. (Previously Presented) The method according to claim 149, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

154. (Previously Presented) The method according to claim 149, wherein the insulating film has a thickness of 50 to 500nm.

155. (Previously Presented) The method according to claim 149, wherein the insulating film has a thickness of 200 to 300nm.

156. (Previously Presented) The method according to claim 149, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

157. (Previously Presented) The method according to claim 149, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

158. (Previously Presented) The method according to claim 149, wherein the leveling film

comprises an inorganic spin on glass material.

159. (Previously Presented) The method according to claim 149, wherein the pixel electrode is made of a conductive oxide film.

160. (Previously Presented) The method according to claim 149, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

161. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film covering a surface of the wiring;

forming a leveling film formed by a spin coating method on the insulating film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

162. (Previously Presented) The method according to claim 161, wherein the wiring is formed by a sputtering method.

163. (Previously Presented) The method according to claim 161, wherein the wiring comprises aluminum.

164. (Currently Amended) The method according to claim 161, wherein the wiring is a three-layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

165. (Previously Presented) The method according to claim 161, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

166. (Previously Presented) The method according to claim 161, wherein the insulating film has a thickness of 50 to 500nm.

167. (Previously Presented) The method according to claim 161, wherein the insulating film has a thickness of 200 to 300nm.

168. (Previously Presented) The method according to claim 161, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

169. (Previously Presented) The method according to claim 161, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

170. (Previously Presented) The method according to claim 161, wherein the leveling film comprises an inorganic spin on glass material.

171. (Previously Presented) The method according to claim 161, wherein the pixel electrode is made of a conductive oxide film.

172. (Previously Presented) The method according to claim 161, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.

173. (Currently Amended) A method of fabricating a display device comprising the steps of:

forming a semiconductor film over a substrate;

forming an interlayer insulating film over the semiconductor film;

forming a wiring connecting to the semiconductor film through a hole in the interlayer insulating film on the interlayer insulating film;

forming an insulating film deposited on the wiring;

forming a leveling film formed by a spin coating method on the insulating film; ~~and~~

forming a pixel electrode over the leveling film; and

forming an electro luminescence layer over the pixel electrode.

174. (Previously Presented) The method according to claim 173, wherein the wiring is formed by a sputtering method.

175. (Previously Presented) The method according to claim 173, wherein the wiring comprises aluminum.

176. (Currently Amended) The method according to claim 173, wherein the wiring is a three-

layered laminate film containing a first ~~tantalum~~ titanium film, an aluminum film and a second ~~tantalum~~ titanium film.

177. (Previously Presented) The method according to claim 173, wherein the insulating film is made of one of a silicon nitride film, a silicon oxide film and a silicon nitride oxide film.

178. (Previously Presented) The method according to claim 173, wherein the insulating film has a thickness of 50 to 500nm.

179. (Previously Presented) The method according to claim 173, wherein the insulating film has a thickness of 200 to 300nm.

180. (Previously Presented) The method according to claim 173, wherein the leveling film has a thickness of 0.1 μm to 1.5 μm.

181. (Previously Presented) The method according to claim 173, wherein the method further comprises a step of forming another leveling film formed by a spin coating method on the leveling film.

182. (Previously Presented)The method according to claim 173, wherein the leveling film comprises an inorganic spin on glass material.

183. (Previously Presented) The method according to claim 173, wherein the pixel electrode is made of a conductive oxide film.

184. (Previously Presented) The method according to claim 173, wherein the display device is used in one selected from the group consisting of a portable phone, a video camera, a computer, and a projector.